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STMicroelectronics BFX34

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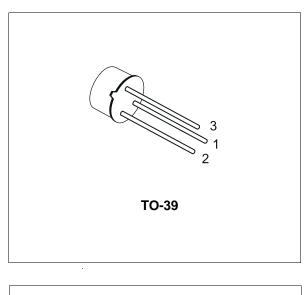
SILICON NPN TRANSISTOR

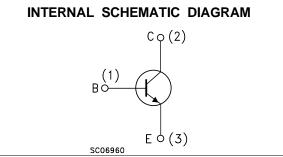
- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR

DESCRIPTION

The BFX34 is a silicon Epitaxial Planar NPN transistor in Jedec TO-39 metal case, intented for high current applications.

Very low saturation voltage and high speed at high current levels make it ideal for power drivers, power amplifiers, switching power supplies and relay drivers inverters.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{СВО}	Collector-Base Voltage $(I_E = 0)$	ctor-Base Voltage ($I_E = 0$) 120	
V_{CEO}	Collector-Emitter Voltage $(I_B = 0)$	ellector-Emitter Voltage (I _B = 0) 60	
V_{EBO}	Emitter-Base Voltage $(I_C = 0)$	6	V
lc	Collector Current	r Current 5	
P _{tot}	Total Dissipation at $T_{case} \le 25$ °C $T_{amb} \le 25$ °C	5 0.87	W W
T _{stg}	Storage Temperature	-65 to 200	°C
Tj	Max. Operating Junction Temperature	200	°C



THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	35	°C/W
R _{thj-amb}	Thermal Resistance Junction-amb	Max	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \, {}^{\circ}C$ unless otherwise specified)

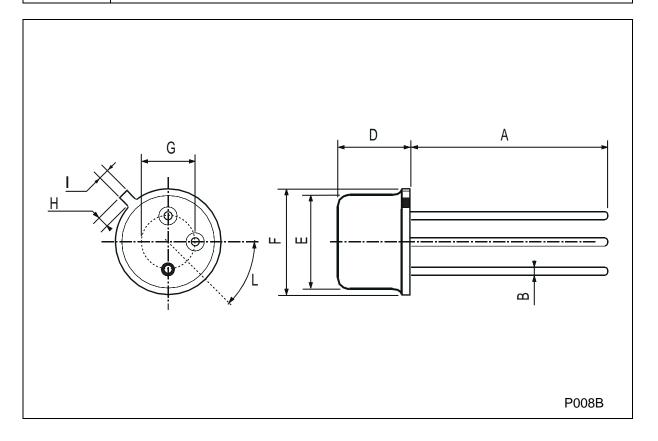
Symbol	Parameter Test Conditions		nditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 60 V			0.02	10	μA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	$V_{EB} = 4 V$			0.05	10	μA
V _{(BR)CBO} *	Collector-base Breakdown Voltage (I _E = 0)	I _C = 5 mA		120			V
$V_{CEO(sus)}^{*}$	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA		60			V
V_{EBO}^{*}	Emitter-base Voltage (I _C = 0)	I _E = 1 mA		6			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 5 A	I _B = 0.5 A		0.4	1	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 5 A	I _B = 0.5 A		1.3	1.6	V
hfe*	DC Current Gain	$I_{C} = 1 A$ $I_{C} = 1.5 A$ $I_{C} = 2 A$	V _{CE} = 2 V V _{CE} = 0.6 V V _{CE} = 2 V	40	100 75 80	150	
f_{T}^{*}	Transition Frequency	I _C = 0.5 A f = 20 MHz	$V_{CE} = 5 V$	70	100		MHz
C _{EBO}	Emitter-base Capacitance	I _C = 0 f = 1 MHz	$V_{EB} = 0.5 V$		300	500	pF
Ссво	Collector-base Capacitance	$I_E = 0$ f = 1 MHz	$V_{CB} = 10 V$		40	100	pF
t _{on} t _{off}	RESISTIVE LOAD Turn-on Time Turn-off Time	$I_{B1} = -I_{B2} = 0.5 \text{ A}$	V _{CC} = 20 V		0.6 0.6	0.25 1.2	μs μs

 \ast Pulsed: Pulse duration = 300 $\mu s,$ duty cycle 1.5 %



DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	12.7			0.500		
В			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
н			1.2			0.047
I			0.9			0.035
L	45° (typ.)					





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